








	<p>SI7892BDP-T1-E3</p>
	<p>Hersteller-Teilenummer: SI7892BDP-T1-E3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 15A PPAK SO-8</p> <p>Datenblätter:  SI7892BDP-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 160993 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7892BDP-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 30V 15A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	160993 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	1.8W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	15A (Ta)
Rds On (Max) @ Id, Vgs	4.2 mOhm @ 25A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	40nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	3775pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)


SI7892BDP-T1-E3 ist neu im Original, Suche SI7892BDP-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7892BDP-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7892BDP-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7892BDP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 15A PPAK SO-8</p>	 <p>SI7892ADP-T1-E3 VISHAY SI7892ADP-T1-E3 VISHAY</p>	 <p>SI7892DP VISHAY SI7892DP VISHAY</p>	 <p>SI7888DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 9.4A PPAK SO-8</p>
 <p>SI7892ADP-T1-GE3. VIS SI7892ADP-T1-GE3. VIS</p>	 <p>SI7888DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 9.4A PPAK SO-8</p>	 <p>SI7892ADP-T1-GE3 V SI7892ADP-T1-GE3 V</p>	 <p>SI7892BDP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 15A PPAK SO-8</p>

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|  SI7882DP-T1-GE3 |  SI7882DP-T1-GE3 |  SI7884BDP |  SI7884BDP-T1-E3 |  SI7884BDP-T1-E3 |
|  SI7884BDP-T1-GE3 |  SI7884BDP-T1-GE3 |  SI7884DP-T1-E3 |  SI7884DP-T1-GE3 |  SI7886ADP-T1-E3 |
|  SI7886ADP-T1-E3 |  SI7886ADP-T1-GE3 |  SI7886ADP-T1-GE3 |  SI7886DP |  SI7886DP-T1 |
|  SI7886DP-T1-E3 |  SI7886DP-T1-GE3 |  SI7888DP-T1-E3 |  SI7888DP-T1-E3 |  SI7888DP-T1-GE3 |
|  SI7888DP-T1-GE3 |  SI7892ADP-T1-E3 |  SI7892ADP-T1-GE3 |  SI7892ADP-T1-GE3. |  SI7892BDP-T1-E3 |
|  SI7892BDP-T1-GE3 |  SI7892BDP-T1-GE3 |  SI7892DP |  SI7892DP-T1 |  SI7892DP-T1-E3 |
|  SI7892DP-T1-GE3 |  SI7898DP |  SI7898DP-T1-E3 |  SI7898DP-T1-E3 |  SI7898DP-T1-GE3 |
|  SI7898DP-T1-GE3 |  SI7900ADN |  SI7900AEDN |  SI7900AEDN-T1 |  SI7900AEDN-T1-E3 |
|  SI7900AEDN-T1-E3 |  SI7900AEDN-T1-GE3 |  SI7900AEDN-T1-GE3 |  SI7900EDN |  SI7900EDN-T1 |
|  SI7900EDN-T1-E3 |  SI7900EDN-T1-GE3 |  SI7901EDN-T1 |  SI7901EDN-T1-E3 |  SI7901EDN-T1-E3 |

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